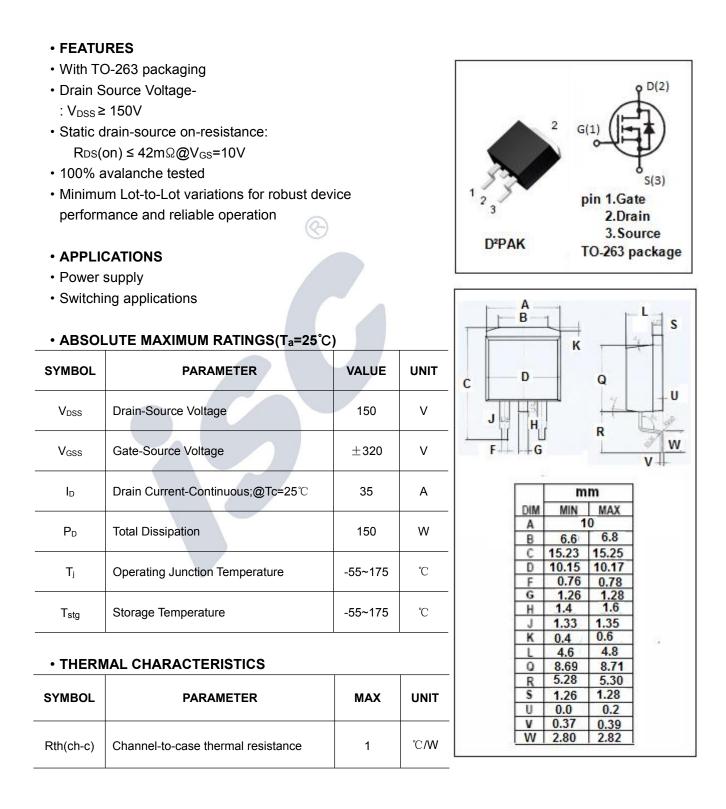


isc N-Channel MOSFET Transistor

FDB42AN15A0



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 250uA	150			V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =250uA	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =12A			42	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 150V; V _{GS} = 0V V _{DS} = 150V; V _{GS} = 0V;TJ=175℃			1 1000	μ Α
VSDF	Diode forward voltage	I _{SD} = 12A, V _{GS} = 0 V			1.25	V

NOTICE:

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